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A

for the charge transport properties of
dressed quantum Hall systems

high-intensity

We present

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(Dated: August 10, 2021)

A generalized mathematical model for predicting the transport properties of a quantum system exposed to a stationary magnetic field and a high intensity electromagnetic field is presented. The new formulation, which applies to two-dimensional(2D) dressed quantum Hall systems, is based on Landau quantization theory and Floquet-Drude conductivity approach. We model our system as a two-dimensional electron gas (2DEG) that interacts with two external fields. To analyze the strong light coupling with the 2DEG, we employ the Floquet theory as a nonperturbative procedure. Moreover, the Floquet-Fermi golden rule is adopted to explore the impurity scattering effects on charge transport in disordered quantum Hall systems. We derive fully analytical expressions to of longitudinal components in the conductivity tensor in dressed quantum Hall systems. Subsequently, we demonstrate that the conductivity characteristics of quantum Hall systems can be manipulated under strong external light. Our results align with well-established and experimentally verified theoretical descriptions for undressed systems while providing a more generalized analysis on the conductivity characteristics in quantum Hall systems. Thus, our model can be applied to accurately interpret the usage of external strong radiation as a tool in nanoscale quantum devices.

spelling
characteristics

strong external

I. INTRODUCTION

Manipulating light-matter interactions in the quantum regime paved the path for an astonishing number of useful technologies in the last century. Quantum optics, which study these interactions, have drawn research attention to the disciplines of optoelectronics [1–4], sensing [5–7], energy harvesting [8, 9], quantum computing [10–12], bio-information [13, 14], and many other specialties of recent technologies [15]. The studies on quantum optics of nanostructures were generally centered on metamaterials [16, 17], quantum plasmonic effects [18, 19], lasers and amplifiers [20, 21], and quantum cavity physics [22, 23]. However, in recent years, one of the foremost aim of examining nanostructures under external radiation was understanding their electron transport characteristics [24–31].

Better understanding the fundamental mechanisms of charge transport can allow us to invent novel nanoelectronic devices and optimize their performance [32]. Most recent studies on the subject have considered the driving field as a perturbation field [27, 28]. However, this assumption breaks down under high-intensity illuminations [31, 33]. Modeling an electromagnetic field under a perturbative formalism involves expanding the interaction terms in powers of the field intensity. At high intensities, the higher order terms influence the physics more strongly and the basis of the perturbative treatment begins to break down. In these instances, a more accurate treatment needs to adopt. Thus, we treat the interacting fermion system and the radiation as one combined quantum system, namely dressed system [28, 34, 35]. Here the applied high-intensity electromagnetic field identify as the dressing field.

Theoretical analyses on the transport properties of

dressed fermion systems were recently reported in Refs. [36–38]. Moreover, in Ref. [31] a general expression for the conductivity in a dressed system has been derived in analytical form. In their study, the authors explore the system's functions, namely four-times the Floquet-Drude conductivity is used to derive the Floquet-Drude conductivity. This opened the path to explore and exploit the charge transport attributes of nanostructures under an intense dressing field.

Quantum Hall effect [36] observed in two-dimensional (2D) fermion systems at low temperatures under strong stationary magnetic fields manifest remarkable magnetotransport behaviors. Transport properties of these systems have recently attracted both theoretical [37–43] and experimental [44–46] interest. Endo *et al.* [43] presented the calculations of longitudinal and transverse conductivity tensor components and their relationship in a quantum Hall system. These theoretical calculations align better with experimental observations to previous studies.

exciting

In contrast, more interesting phenomena can be observed by simultaneously applying a dressing field to a quantum Hall system already under a non-oscillating magnetic field. Whilst there exist several leading theories for calculating conductivity tensor elements in quantum Hall systems [38, 42, 43], they have not been utilized to describe the optical manipulation of charge transport. Recently, Dini *et al.* [30] have investigated the one-directional conductivity behavior of dressed quantum Hall systems. However, they have not adopted the state-of-the-art model to describe the conductivity in a quantum Hall system. In their study, they used the conductivity models from Refs. [38, 42], and as mentioned in Endo *et al.* [43], those models predict a semi-elliptical broadening against Fermi level for each Landau levels and

against

level

provide less agreement with the empirical results.

In the present analysis, we present a robust mathematical model for a dressed two-dimensional electron gas (2DEG) subject to another nonoscillating magnetic field. A stationary magnetic field is applied perpendicularly across the surface of the 2DEG system. This causes the orbital motion of the electrons to be quantized, and a discrete energy spectrum with Landau splitting is observed [47]. In this study, we explicitly calculate the longitudinal components (σ^{xx} , σ^{yy}) of the conductivity tensor in a periodically driven quantum Hall system by developing a generalized analytical description using the Floquet-Drude conductivity [31]. Finally, we demonstrate that our generalized model reproduces the results of the state-of-the-art conductivity model in Ref. [43], which was developed for the more specific case of quantum Hall systems without the external dressing field. Moreover, we find that the optical field can be used as a mechanism to regulate transport behavior in numerous 2D nanostructures which can serve as a basis for many useful nanoelectronic devices. We believe that our theoretical analysis and visual depictions of numerical results will lead to a better understanding of many phenomena and introduces port. Moreover, this will inspire advanced developments in nanoscale quantum devices.

The paper is organized as follows. In Sec. II, we introduce our dressed quantum Hall system and the exact wave function solutions for the given configuration. Sec. III provides the Floquet theory interpretation of these wave functions. We introduce Floquet-Fermi golden rule for a quantum Hall system in Sec. IV, and use it in Sec. V to derive analytical expressions for longitudinal components of conductivity. The derived theoretical model is further analyzed numerically using empirical system parameters and compared with previous studies in Sec. VI. In Sec. VII, we summarize our analysis and present our conclusions.

II. SCHRÖDINGER PROBLEM FOR A DRESSED QUANTUM HALL SYSTEM

Our system consists of a 2DEG placed on the xy -plane of the three-dimensional coordinate space. In our analysis, the 2DEG is subjected to a nonoscillating magnetic field $\mathbf{B} = (0, 0, B)^T$ which is pointed towards the z axis. In addition, a linearly polarized strong light is applied perpendicular to the 2DEG surface. We specially select the frequency of the dressing field ω to be in the off-resonant regime such that the field behaves as a purely dressing field. Furthermore, without limiting the generality we choose y -polarized electric field $\mathbf{E} = (0, E \sin(\omega t), 0)^T$ for the linearly polarized dressing field (Fig. 1). Here B and E represent the amplitudes of the stationary magnetic field and oscillating electric field respectively.

Using Landau gauge for the stationary magnetic field, we can represent it as a vector potential $\mathbf{A}_s =$

we can represent our system

$(-By, 0, 0)^T$. Furthermore, we consider a dressing field in the Coulomb gauge $(0, [E/\omega] \cos(\omega t), 0)^T$. These vector potentials are added to the momentum of 2DEG as kinetic momentum [48, 49]. Thus, our system can be represented with a time-dependent Hamiltonian

$$\hat{H}_e(t) = \frac{1}{2m_e} [\hat{\mathbf{p}} - e[\mathbf{A}_s + \mathbf{A}_d(t)]]^2, \quad (1)$$

where m_e is the effective electron mass, e is the magnitude of the electron charge, and $\hat{\mathbf{p}} = (\hat{p}_x, \hat{p}_y, 0)^T$ represents the canonical momentum operator for 2DEG with electron momentum $(p_x, p_y, 0)^T$. The exact solutions for the time-dependent Schrödinger equation $i\hbar \frac{d\psi}{dt} = \hat{H}_e(t)\psi$ were given in Ref. [30, 50, 51]. Here we present the exact solutions defined by two quantum numbers n and m .

$$\begin{aligned} \psi_{n,m}(x, y, t) &= \frac{1}{\sqrt{L_x L_y}} \exp\left(\frac{i}{\hbar} \left[-\epsilon_n t + p_x x + \frac{y - y_0}{\omega} \cos(\omega t) \right. \right. \\ &\quad \left. \left. + \int_0^t dt' L(\zeta, \dot{\zeta}, t') \right] \right), \end{aligned} \quad (2)$$

where $n \in \mathbb{Z}_0^+$ and $m \in \mathbb{Z}$. Here L_x and L_y are dimensions of the 2DEG surface, and \hbar is the reduced Planck constant. The center of the cyclotron orbit on the y -axis is given by $y_0 = -p_x/eB$ with $p_x = 2\pi\hbar m/L_x$. Moreover, χ_n are well-known eigenstate solutions for the Schrödinger equation of the stationary quantum harmonic oscillator

$$\chi_n(y) = \frac{\sqrt{\kappa}}{\sqrt{2^n n!}} e^{-\kappa^2 y^2/2} \mathcal{H}_n(\kappa y), \quad (3)$$

with eigenvalues $\epsilon_n = \hbar\omega_0(n+1/2)$ where $\kappa = \sqrt{m_e\omega_0/\hbar}$, $\mathcal{H}_n(\cdot)$ is the n -th Hermite polynomial, and the cyclotron frequency $\omega_0 = eB/m_e$. The path shift of the driven

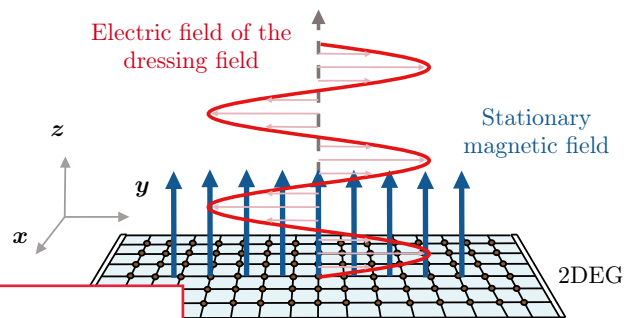


FIG. 1. Our 2DEG system only confined in the (x, y) plane while both stationary magnetic field \mathbf{B} and dressing field (with y -polarized electric field \mathbf{E}) are applied perpendicular to the surface of 2DEG.

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Kosala, here time derivative is explicitly written but then eq. 2 uses a dot? There is some issue in consistent notation here!!

well-known

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conclusions.

a

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classical oscillator $\zeta(t)$ is given by

$$\zeta(t) = \frac{eE}{m_e(\omega_0^2 - \omega^2)} \sin(\omega t), \quad (4)$$

while the Lagrangian of the driven classical oscillator $L(\zeta, \dot{\zeta}, t)$ can be identified as

$$L(\zeta, \dot{\zeta}, t) = \frac{1}{2}m_e\dot{\zeta}^2(t) - \frac{1}{2}m_e\omega_0^2\zeta^2(t) + eE\zeta(t)\sin(\omega t). \quad (5)$$

For details of the full derivation refer to Appendix A. The exponential phase shifts in Eq. (2) represent the influence of the stationary magnetic field and dressing field on the electron behavior of our system. Therefore, we can observe that the magneto-transport characteristics of 2DEG can be renormalized by a nonoscillating magnetic field along with a dressing field.

give

III. FLOQUET THEORY PERSPECTIVE

Symmetry conditions often gives useful insights into the behaviors of physical quantum systems. For instance, in the famous Bloch analysis of electrons in quantum systems a mathematical explanation for quantum systems occupying a discrete translational configuration space. Similarly, Floquet theory gives a mathematical formalism that can be used for translational symmetry in time rather than in space [33, 52, 53]. The Floquet-Drude conductivity theory was employed recently by Wackerl *et al.* [31] as a method to analyze the transport properties of quantum systems exposed to strong radiation. In their work, they have presented more accurate results than the former theoretical descriptions for the conductivity of nanoscale systems in the presence of a dressing field. Therefore, we apply the Floquet-Drude conductivity to our 2DEG system which is subjected to both a stationary magnetic field and a dressing field.

First, we need to identify the *quasienergies* and time periodic *Floquet modes* [33] for the wave functions given in Eq. (2). By factorizing the wave function into a linearly time dependent part and a periodic time dependent part, we present the quasienergies as

$$\varepsilon_n = \hbar\omega_0\left(n + \frac{1}{2}\right) - \Delta_\varepsilon, \quad (6)$$

which only depends on a single quantum number n . The Floquet modes can then be recognized as

$$\begin{aligned} \phi_{n,m}(x, y, t) = & \frac{1}{\sqrt{L_x}} \chi_n(y - y_0 - \zeta(t)) \\ & \times \exp\left(\frac{i}{\hbar} \left[p_x x + \frac{eE[y - y_0]}{\omega} \cos(\omega t) \right. \right. \\ & \left. \left. + m_e \dot{\zeta}(t) [y - y_0 - \zeta(t)] + \xi \right] \right), \end{aligned} \quad (7)$$

You have this derivation in the appendix B, why not refer it here to aid the reader?

with

$$\Delta_\varepsilon = \frac{(eE)^2}{4m_e(\omega_0^2 - \omega^2)}, \quad (8)$$

and

$$\xi = \frac{(eE)^2(3\omega^2 - \omega_0^2)}{8m_e\omega(\omega_0^2 - \omega^2)^2} \sin(2\omega t). \quad (9)$$

It is important to note that these Floquet modes are time-periodic ($T = 2\pi/\omega$) functions. At resonance $\omega = \omega_0$, the energy levels occupy a continuous spectrum and the quasienergy formalism is no longer valid [54]. Therefore, in this work we choose a dressing field frequency obeying the condition $\omega \neq \omega_0$.

Performing the Fourier transform over the confined 2D space, we obtain the momentum space (k_x, k_y) representation of Floquet modes

$$\begin{aligned} \phi_{n,m}(k_x, k_y, t) = & \sqrt{L_x} \tilde{\chi}_n(k_y - b \cos(\omega t)) \\ & \times \exp(i\xi - ik_y[d \sin(\omega t) + y_0]), \end{aligned} \quad (10)$$

where

$$\tilde{\chi}_n(k) = \frac{i^n}{\sqrt{2^n n! \sqrt{\pi}}} \left(\frac{1}{\kappa}\right)^{1/2} e^{-\frac{\kappa^2}{2}} \mathcal{H}_n\left(\frac{k}{\kappa}\right). \quad (11)$$

Here we have introduced new parameters

$$b = \frac{eE\omega_0^2}{\hbar\omega(\omega_0^2 - \omega^2)}, \quad (12)$$

and

$$\begin{aligned} & \text{Ahh: you have said it here. Leave this but also say this close to Eq. 7. So, it is easy to read.} \end{aligned} \quad (13)$$

For a detailed derivation, see Appendix B. Using Floquet theory, the wave functions derived in Eq. (2) can be written as Floquet states in momentum space as

$$\psi_{n,m}(k_x, k_y, t) = \exp\left(-\frac{i}{\hbar} \varepsilon_n t\right) \phi_{n,m}(k_x, k_y, t). \quad (14)$$

IV. INVERSE SCATTERING TIME ANALYSIS

The Floquet-Fermi golden rule was proposed in Ref. [31] as an approach to analyze the transport properties of dressed quantum systems with impurities. However, this theory has not been applied for a dressed quantum Hall system in the previous studies. In this analysis, we use Floquet-Fermi golden rule to identify the effects induced by impurities on the magneto-transport properties. With the help of $t - t'$ formalism [31, 33, 55–57] and applying Floquet states derived in Eq. (14), we can derive an expression for (l, l') -th element of the inverse

scattering time matrix for the N -th Landau level as

$$\begin{aligned} & \left(\frac{1}{\tau(\varepsilon, k_x)} \right)_N^{ll'} \\ & - \frac{\varrho^2}{\delta(\varepsilon - \varepsilon_N)} \\ & \times \int_{-\infty}^{\infty} dk_1 \left[J_l \left(\frac{b\hbar}{eB} [k_x - k_1] \right) J_{l'} \left(\frac{b\hbar}{eB} [k_x - k_1] \right) \right. \\ & \times \left. \left| \int_{-\infty}^{\infty} dk_2 \chi_N \left(\frac{\hbar}{eB} k_2 \right) \chi_N \left(\frac{\hbar}{eB} [k_1 - k_x - k_2] \right) \right|^2 \right], \end{aligned} \quad (15)$$

where $\varrho = \eta_{imp} L_x [V_{imp}/eB]^{1/2}$, ε is a given energy value. $J_l(\cdot)$ are Bessel functions of the first kind with order l and ε_N is the energy of the N -th Landau level. A more detailed derivation is given in Appendix C. We modeled the effect caused by impurities in the considered system as a single perturbation potential. Since random impurities in a disordered metal offers a better

, for experimental conditions, we assumed that our perturbation potential is formed by a group of randomly distributed impurities. Thus, the total scattering potential in the 2DEG has been represented as a sum of uncorrelated single impurity potentials $v(\mathbf{r})$. Here η_{imp} is the number of impurities in a unit area, $V_{imp} = \langle |V_{k'_x, k_x}|^2 \rangle_{imp}$ with $V_{k'_x, k_x} = \langle k'_x | v(x) | k_x \rangle$, and $\langle x | k_x \rangle = e^{-ik_x x}$. Moreover in this analysis, $\langle \cdot \rangle_{imp}$ represents the average over the impurity disorder.

Next, we analyze the scattering time matrix elements. Since the disorder in the system can not significantly alter the eigenenergy values of the undressed system [31], we can neglect the contribution of all off-diagonal elements in the inverse scattering time matrix. Subsequently we consider only the central ($l = l' = 0$) diagonal element of the inverse scattering time matrix which has the largest contribution to the transport characteristics. Along with this assumption, we introduce a new parameter as the scattering-induced broadening of the N -th Landau level [30, 43]

$$\Gamma_N^{00}(\varepsilon, k_x) = \hbar \left(\frac{1}{\tau(\varepsilon, k_x)} \right)_N, \quad (16)$$

which simplifies to

$$\begin{aligned} & \Gamma_N^{00}(\varepsilon, k_x) \\ & = \frac{\varrho^2}{eB} \delta(\varepsilon - \varepsilon_N) \\ & \times \int_{-\infty}^{\infty} dk_1 \left[J_0^2 \left(\frac{b\hbar}{eB} [k_x - k_1] \right) \right. \\ & \times \left. \left| \int_{-\infty}^{\infty} dk_2 \chi_N \left(\frac{\hbar}{eB} k_2 \right) \chi_N \left(\frac{\hbar}{eB} [k_1 - k_x - k_2] \right) \right|^2 \right]. \end{aligned} \quad (17)$$

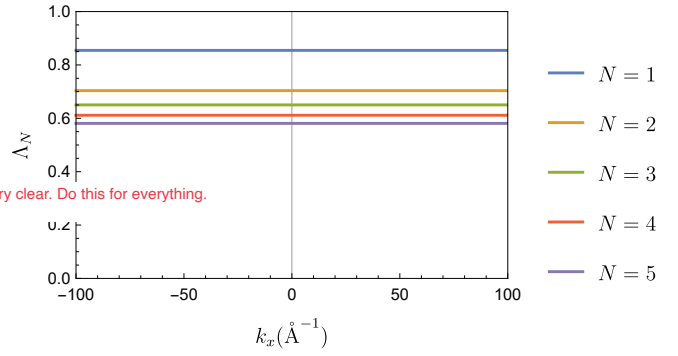


FIG. 2. The dependence of normalized scattering-induced broadening Λ_N for each Landau level ($N = 0, 1, 2, 3, 4$) on the x -directional momentum k_x within spelling based quantum well under a nonoscillating magnetic field with $B = 1.2$ T, dressing field with frequency of $\omega = 2 \times 10^{12}$ rads^{-1} and intensity $I = 100$ W/cm^2 . In this calculation we have assumed that the natural broadening of 0-th Landau level Γ_0 is 0.24 meV.

In addition, for a scattering scenario taking place within the same Landau level, we are able to present the delta distribution of the energy by the interpretation [30]

$$\delta(\varepsilon - \varepsilon_N) = \frac{1}{2\pi} \int_{-\infty}^{\infty} dt e^{i(\varepsilon - \varepsilon_N)t} \quad (18)$$

Then we write the inverse scattering time matrix in the more compact form

$$\begin{aligned} \Gamma_N^{00}(\varepsilon, k_x) & = \varrho \left[\int_{-\infty}^{\infty} dk_1 J_0^2(\lambda_1[k_x - k_1]) \right. \\ & \times \left. \left| \int_{-\infty}^{\infty} dk_2 \tilde{\chi}_N(\lambda_2 k_2) \tilde{\chi}_N(\lambda_2[k_1 - k_2 - k_x]) \right|^2 \right]^{-\frac{1}{2}}, \end{aligned} \quad (19)$$

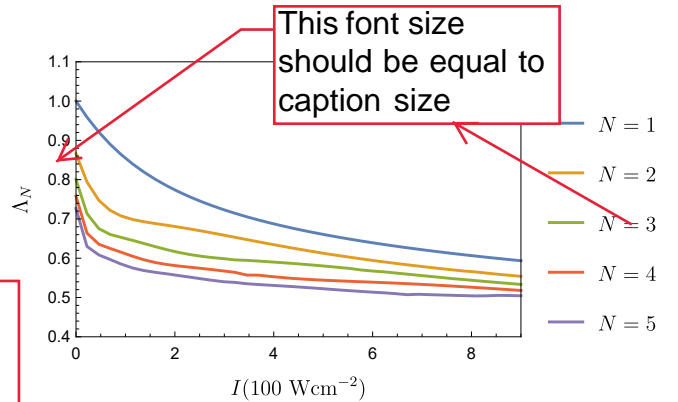


FIG. 3. The dependence of normalized scattering-induced broadening Λ_N for each Landau level ($N = 0, 1, 2, 3, 4$) against dressing field intensity I , in a GaAs-based quantum well under a nonoscillating magnetic field with $B = 1.2$ T, dressing field with frequency of $\omega = 2 \times 10^{12}$ rads^{-1} . In this calculation we have assumed that the natural broadening of 0-th Landau level Γ_0 is 0.24 meV.

where $\lambda_1 \equiv \hbar b/eB$ and $\lambda_2 \equiv \hbar \kappa/eB$. To analyze the effects of the dressing field on the scattering-induced broadening, we introduce the normalized N -th Landau level scattering-induced broadening as

$$\Lambda_N(k_x) = \frac{\Gamma_N^{00}(\varepsilon, k_x)}{\Gamma_{N=0}^{00}(\varepsilon, k_x)|_{E=0}}, \quad (20)$$

$$\Lambda_N(k_x) = \left[\frac{\int_{-\infty}^{\infty} dk_1 J_0^2(\lambda_1[k_x - k_1]) \left| \int_{-\infty}^{\infty} dk_2 \tilde{\chi}_N(\lambda_2 k_2) \tilde{\chi}_N(\lambda_2[k_1 - k_2 - k_x]) \right|^2}{\int_{-\infty}^{\infty} dk_1 \left| \int_{-\infty}^{\infty} dk_2 \tilde{\chi}_0(\lambda_2 k_2) \tilde{\chi}_0(\lambda_2[k_1 - k_2 - k_x]) \right|^2} \right]^{1/2}. \quad (21)$$

Normalized energy band broadening against x -directional momentum component k_x for different Landau levels ($N = 0, 1, 2, 3, 4$) in the GaAs-based quantum well and the results are depicted in Fig. (2) and Fig. (3). To make a comparison, we have selected the experiment parameters to match with analysis in Ref. [43]. In that study, the authors have assumed that effective mass of the electron in GaAs-based quantum well system is $m_e \approx 0.07\tilde{m}_e$ where \tilde{m}_e is mass of the electron [31, 43, 58]. In addition, they used the broadening of the undressed 0-th Landau level Γ_0 as 0.24 meV. Therefore, in our calculations, we assumed that the natural least Landau level broadening also has this value: $\Gamma_{N=0}^{00}|_{E=0} = 0.24$ meV. Here, we observe that the normalized energy broadening value for $N=0$ is independent of the x -directional momentum k_x value and we are able to manipulate it by the dressing field. When the dressing field's intensity increases, the energy broadening is reduced, which leads to changes in the transport properties of the dressed quantum Hall system. To analyze these adjustments in detail, we derive an analytical expression for the conductivity of a dressed quantum Hall system in the next section.

V. FLOQUET-DRUDE CONDUCTIVITY IN A DRESSED QUANTUM HALL SYSTEM

A general theory for the conductivity of a system with the disorder averaging was reported

$$\sigma^{xx} = \frac{-1}{4\pi\hbar A} \int_{\Pi-\hbar\omega/2}^{\Pi+\hbar\omega/2} d\varepsilon \left(-\frac{\partial f}{\partial \varepsilon} \right) \frac{1}{V_{k_x}} \sum_{k_x} \sum_n \langle n, k_x | j_0^x(\mathbf{G}^r(\varepsilon) - \mathbf{G}^a(\varepsilon)) j_0^x(\mathbf{G}_0^r(\varepsilon) - \mathbf{G}_0^a(\varepsilon)) | n, k_x \rangle, \quad (24)$$

where V_{k_x} is the volume of considering x -directional momentum space. Next, we evaluate the above expression as follows

$$\sigma^{xx} = \frac{-1}{4\pi\hbar A} \int_{\Pi-\hbar\omega/2}^{\Pi+\hbar\omega/2} d\varepsilon \left(-\frac{\partial f}{\partial \varepsilon} \right) \frac{1}{V_{k_x}^4} \sum_{k_x} \sum_n \sum_{k_{x1}, k_{x2}, k_{x3}} \sum_{n_1, n_2, n_3} \langle n, k_x | j_0^x | n_1, k_{x1} \rangle \langle n_1, k_{x1} | (\mathbf{G}^r(\varepsilon) - \mathbf{G}^a(\varepsilon)) | n_2, k_{x2} \rangle \langle n_2, k_{x2} | j_0^x | n_3, k_{x3} \rangle \langle n_3, k_{x3} | (\mathbf{G}^r(\varepsilon) - \mathbf{G}^a(\varepsilon)) | n, k_x \rangle. \quad (25)$$

which can be evaluated with

change the integral notation

et al. [31, 59]. This theory, the general x -directional longitudinal DC-limit conductivity has been characterized as

$$\sigma^{xx} = \frac{-1}{4\pi\hbar A} \int_{\Pi-\hbar\omega/2}^{\Pi+\hbar\omega/2} d\varepsilon \left[\left(-\frac{\partial f}{\partial \varepsilon} \right) \times \text{tr} [j_0^x(\mathbf{G}^r(\varepsilon) - \mathbf{G}^a(\varepsilon)) j_0^x(\mathbf{G}^r(\varepsilon) - \mathbf{G}^a(\varepsilon))] \right], \quad (22)$$

where j_0^x and $\mathbf{G}^{r,a}(\varepsilon)$ are the x -directional electric current operator matrix elements' 0-th Fourier component and the white noise disorder averaged Floquet Green function matrix [31, 59] respectively defined against the Floquet modes of the considering system. Here we have assumed that only 0-th Fourier component of the current operator is contributing to the conductivity. In addition, A is the area of the considered two-dimensional system, f is the partial distribution function, the that can be chosen such that

$$\Pi - \frac{\hbar\omega}{2} \leq \varepsilon_N < \Pi + \frac{\hbar\omega}{2}. \quad (23)$$

Here ε_N are quasienergies of all relevant Floquet states, and $\text{tr}[\cdot]$ is the trace of the considering operator.

Next, we restrict our analysis into off-resonant regime ($\omega\tau_0 \gg 1$), where τ_0 is the scattering time of the undriven system. Thus, the x -directional longitudinal conductivity in Eq. (22) can be expanded using only the entry Fourier components ($l = l' = 0$) of Floquet states $|n, m\rangle \equiv |n, k_x\rangle$ as

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We can diagonalize the impurity averaged Green's functions using a unitary transformation ($\mathbf{T} \equiv |n, k_x\rangle$) as mentioned in Refs. [31, 59, 60]. Thus, we evaluate the matrix elements of the difference between retarded and advanced Green's functions as

$$\langle n_1, k_{x1} | \mathbf{T}^\dagger (\mathbf{G}^r(\varepsilon) - \mathbf{G}^a(\varepsilon)) \mathbf{T} | n_2, k_{x2} \rangle = \left[\frac{2i \text{Im}(\mathbf{T}^\dagger \mathbf{\Sigma}^r \mathbf{T}) \delta_{n_1, n_2} \delta_{k_{x1}, k_{x2}}}{\left(\frac{1}{\hbar} \varepsilon - \frac{1}{\hbar} \varepsilon_{n_1}\right)^2 + [\text{Im}(\mathbf{T}^\dagger \mathbf{\Sigma}^r \mathbf{T})]^2} \right], \quad (26)$$

and

$$\langle n_3, k_{x3} | \mathbf{T}^\dagger (\mathbf{G}^r(\varepsilon) - \mathbf{G}^a(\varepsilon)) \mathbf{T} | n, k_x \rangle = \left[\frac{2i \text{Im}(\mathbf{T}^\dagger \mathbf{\Sigma}^r \mathbf{T}) \delta_{n_3, n} \delta_{k_{x3}, k_x}}{\left(\frac{1}{\hbar} \varepsilon - \frac{1}{\hbar} \varepsilon_n\right)^2 + [\text{Im}(\mathbf{T}^\dagger \mathbf{\Sigma}^r \mathbf{T})]^2} \right]. \quad (27)$$

Here we introduced the retarded self-energy matrix $\mathbf{\Sigma}^r$ which is the sum of all irreducible diagrams [31, 59]. Applying the matrix elements of the electric current operator in Landau levels and expressions from Eq. (26) and Eq. (27) back into Eq. (25) we obtain

$$\begin{aligned} \sigma^{xx} = & \frac{-1}{4\pi\hbar A} \int_{\Pi-\hbar\omega/2}^{\Pi+\hbar\omega/2} d\varepsilon \left(-\frac{\partial f}{\partial \varepsilon} \right) \frac{1}{V_{k_x}} \sum_{k_x} \sum_n \sum_{n_1, n_2} \\ & \times \frac{e^2 B}{m_e} \left(\sqrt{\frac{n+1}{2}} \delta_{n_1, n+1} + \sqrt{\frac{n}{2}} \delta_{n_1, n-1} \right) \left[\frac{2i \text{Im}(\mathbf{T}^\dagger \mathbf{\Sigma}^r \mathbf{T}) \delta_{n_1, n_2}}{\left(\frac{1}{\hbar} \varepsilon - \frac{1}{\hbar} \varepsilon_{n_1}\right)^2 + [\text{Im}(\mathbf{T}^\dagger \mathbf{\Sigma}^r \mathbf{T})]^2} \right] \\ & \times \frac{e^2 B}{m_e} \left(\sqrt{\frac{n_2+1}{2}} \delta_{n, n_2+1} + \sqrt{\frac{n_2}{2}} \delta_{n, n_2-1} \right) \left[\frac{2i \text{Im}(\mathbf{T}^\dagger \mathbf{\Sigma}^r \mathbf{T})}{\left(\frac{1}{\hbar} \varepsilon - \frac{1}{\hbar} \varepsilon_n\right)^2 + [\text{Im}(\mathbf{T}^\dagger \mathbf{\Sigma}^r \mathbf{T})]^2} \right], \end{aligned} \quad (28)$$

For the full derivation of electric current operators in quantum Hall system refer to Appendix D. After the expansion, the only non-zero term would be

$$\begin{aligned} \sigma^{xx} = & \frac{-1}{4\pi\hbar A} \frac{e^4 B^2}{m_e^2} \int_{\Pi-\hbar\omega/2}^{\Pi+\hbar\omega/2} d\varepsilon \left(-\frac{\partial f}{\partial \varepsilon} \right) \frac{1}{V_{k_x}} \sum_{k_x} \sum_n (n+1) \\ & \times \left[\frac{2i \text{Im}(\mathbf{T}^\dagger \mathbf{\Sigma}^r \mathbf{T})_{\varepsilon_{n+1}}}{\left(\frac{1}{\hbar} \varepsilon - \frac{1}{\hbar} \varepsilon_{n+1}\right)^2 + [\text{Im}(\mathbf{T}^\dagger \mathbf{\Sigma}^r \mathbf{T})_{\varepsilon_{n+1}}]^2} \right] \left[\frac{2i \text{Im}(\mathbf{T}^\dagger \mathbf{\Sigma}^r \mathbf{T})_{\varepsilon_n}}{\left(\frac{1}{\hbar} \varepsilon - \frac{1}{\hbar} \varepsilon_n\right)^2 + [\text{Im}(\mathbf{T}^\dagger \mathbf{\Sigma}^r \mathbf{T})_{\varepsilon_n}]^2} \right]. \end{aligned} \quad (29)$$

The inverse scattering time matrix is equal to the diagonalized contrast of the retarded and advanced self-energy [31, 59]. In addition, on the diagonal the contrast of the retarded and advanced Green's function can be represented with the imaginary component of the retarded self-energy [31, 59]. Subsequently, we can identify the following property

$$\left(\frac{1}{\tau(\varepsilon, k_x)} \right)^u = -2 \text{Im}[\mathbf{T}^\dagger \mathbf{\Sigma}^r(\varepsilon, k_x) \mathbf{T}]^u. \quad (30)$$

Afterwards, considering only the central element ($l = 0$) of the inverse scattering time matrix, we can restructure the derived conductivity expression in 29 as follows

$$\sigma^{xx} = \frac{1}{\pi\hbar A} \frac{e^4 B^2}{m_e^2} \int_{\Pi-\hbar\omega/2}^{\Pi+\hbar\omega/2} d\varepsilon \left(-\frac{\partial f}{\partial \varepsilon} \right) \frac{1}{V_{k_x}} \sum_{k_x} \sum_n (n+1) \left[\frac{\tilde{\Gamma}(\varepsilon_{n+1})}{(\varepsilon_F - \varepsilon_{n+1})^2 + \tilde{\Gamma}^2(\varepsilon_{n+1})} \right] \left[\frac{\tilde{\Gamma}(\varepsilon_n)}{(\varepsilon_F - \varepsilon_n)^2 + \tilde{\Gamma}^2(\varepsilon_n)} \right], \quad (31)$$

with $\tilde{\Gamma}(\varepsilon_n, k_x) \equiv (\hbar/2\tau(\varepsilon_n, k_x))^{00}$. Since we already identified that the inverse scattering time matrix's central element is independent of k_x value, we can drop the k_x -dependent in the $\tilde{\Gamma}(\varepsilon_n, k_x)$ terms and get the sum over all available momentum space in x direction. However, by considering the condition that the center of the cy-

clotron orbit y_0 must physically lie within the considered system, we can identify that

$$-\frac{m_e \omega_0 L y}{2\hbar} \leq k_x \leq \frac{m_e \omega_0 L y}{2\hbar}. \quad (32)$$

We use the Fermi-Dirac distribution as our partial dis-

tribution function (f) for our system

$$f(\varepsilon) = \frac{1}{[\exp(\varepsilon - \varepsilon_F)/k_B T] + 1}, \quad \text{the Boltzmann}$$

where k_B is the Boltzmann constant, T is the absolute temperature and ε_F is the Fermi energy of the system. Considering the above distribution for extremely low temperature conditions, we can use the following approximation

$$-\frac{\partial f(\varepsilon)}{\partial \varepsilon} \approx \delta(\varepsilon - \varepsilon_F). \quad (34)$$

Moreover, let $\Pi = \varepsilon_F$ and the derived expression in 31 leads to

$$\sigma^{xx} = \frac{e^2}{\hbar} \frac{1}{\pi A} \sum_n \frac{(n+1)}{\gamma_n \gamma_{n+1}} \times \left[\frac{1}{1 + \left(\frac{X_F - n - 1}{\gamma_{n+1}} \right)^2} \right] \left[\frac{1}{1 + \left(\frac{X_F - n}{\gamma_n} \right)^2} \right], \quad (35)$$

where $X_F \equiv (\varepsilon_F/\hbar\omega_0 - 1/2)$ and $\gamma_n \equiv \tilde{\Gamma}(\varepsilon_n)/\hbar\omega_0$. Following the same steps as above derivation, we can derive the longitudinal conductivity in y -direction by applying the electric current operator for y -direction derived in Appendix D

$$\sigma^{yy} = \frac{e^2}{\hbar} \frac{1}{\pi A} \frac{1}{e^2 B^2} \sum_n \frac{(n+1)}{\gamma_n \gamma_{n+1}} \times \left[\frac{1}{1 + \left(\frac{X_F - n - 1}{\gamma_{n+1}} \right)^2} \right] \left[\frac{1}{1 + \left(\frac{X_F - n}{\gamma_n} \right)^2} \right]. \quad (36)$$

VI. MANIPULATE QUANTUM HALL SYSTEMS

To identify the longitudinal conductivity characteristics of quantum Hall system under external dressing field, first we derive an expression for normalized longitudinal conductivity as a function of intensity of the dressing field I . Here, we derive the x -directional conductivity of the system using the natural broadening of the Landau level

$$\tilde{\sigma}^{xx} = \sigma_0 \sum_n \frac{(n+1)}{0.0037 \Lambda_n \Lambda_{n+1}} \times \left[\frac{1}{1 + \left(\frac{X_F - n - 1}{0.06 \Lambda_{n+1}} \right)^2} \right] \left[\frac{1}{1 + \left(\frac{X_F - n}{0.06 \Lambda_{n+1}} \right)^2} \right], \quad (37)$$

with $\sigma^0 = e^2/\pi\hbar A$.

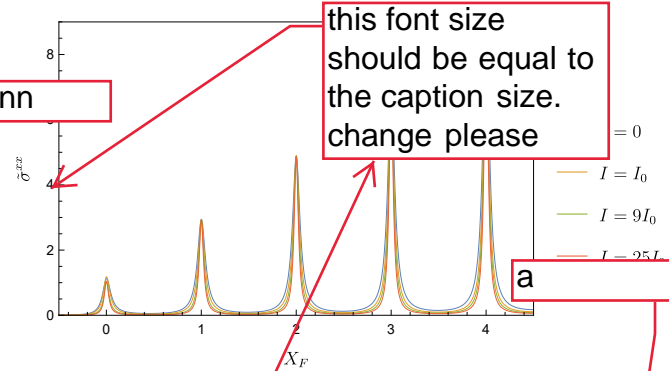


FIG. 4. Normalized longitudinal conductivity $\tilde{\sigma}^{xx}$ against Fermi level X_F with different intensities I of the external dressing field in a GaAs-based quantum well under a nonoscillating magnetic field with $B = 1.2$ T, dressing field with frequency of $\omega = 2 \times 10^{12}$ rads $^{-1}$ and $I_0 = 100$ W/cm 2 . In this calculation we have assumed that the natural broadening of 0-th Landau level Γ_0 is 0.24 meV.

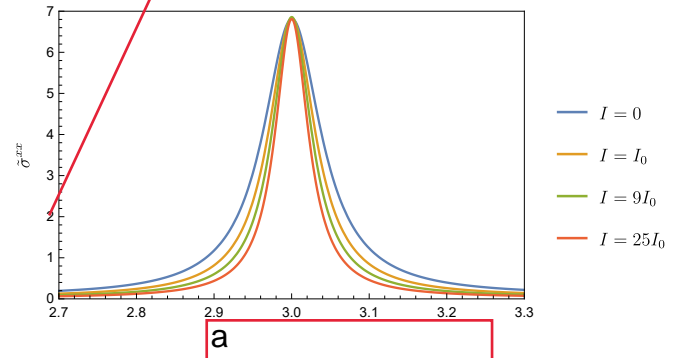


FIG. 5. 3rd Landau level's normalized longitudinal conductivity $\tilde{\sigma}^{xx}$ against Fermi level X_F with different intensities I of the external dressing field in a GaAs-based quantum well under a nonoscillating magnetic field with $B = 1.2$ T, dressing field with frequency of $\omega = 2 \times 10^{12}$ rads $^{-1}$ and $I_0 = 100$ W/cm 2 . In this calculation, the natural broadening of 0-th Landau level Γ_0 is 0.24 meV.

As illustrated in Fig. 4 and 5, we can observe that the normalized longitudinal conductivity $\tilde{\sigma}^{xx}$ varies with the applied dressing field's intensity and the Fermi level X_F of the considered system. For a given dressing field intensity, the longitudinal conductivity varies with the Fermi level of the system showing sharp peaks at each Landau energy level. In quantum Hall systems, electrons are restricted to bear only the Landau energy levels. The longitudinal conductivity reduces significantly when the Fermi level is not aligned with any of the Landau levels. In contrast, near each Landau level, the conductivity achieves excessive values compared to other areas. Moreover, as illustrates in Fig. 4, the peak value of the normalized longitudinal conductivity on each Landau level gets increase with the Landau level number.

On the other hand, considering the effects of the ap-

publication

illustrated

Fig.

plied dressing field on the longitudinal conductivity of 2DEG, we can identify that the dressing field has sharpened the conductivity peaks. When we increase the intensity level of the dressing field, the conductivity regions get more weakened as illustrated in the 5. However, the peak value of the conductivity at each Landau level has the same value as the undressed system. This demonstrates our ability to tune the width of the conductivity regions in these quantum Hall systems with the help of a dressing

These characteristics align well with the outcomes demonstrated by Dini *et al.* [30]. As the authors remarked in that work, since the Fermi level of the system can be changed with the applied gate voltage of the material this can be utilized as a 2D switch for nanoscale optoelectronics applications. Controlling the external dressing field's intensity allows us to fine-tune

Fig.

g mechanism for an optimized performance.

However, we can distinguish that the shapes and behavior of the conductivity regions illustrated in Fig. 4 and 5 are generally incompatible with the results ref. [30]. This is due to the selection of the

are

conventional longitudinal conductivity theory of 2DEG from Refs. [38, 42]. The semi-elliptical conductivity regions illustrated in Refs. [30, 38, 42], have less consistency with the experimentally observed data for Landau levels [43]. In our study of the transport properties of quantum Hall system we developed the conductivity expression starting from

experimentally spelling

for

we achieved outcomes that align with the results adopted in Ref. [43]. The theory on the conductivity of quantum Hall systems in Ref. [43] provides an excellent agreement with the experimentally observed results in GaAs/AlGaAs 2DEG for the low magnetic field range. However, they have not considered the tunability that can be achieved with a dressing field. In this analysis, we account both of the magnetic and dressing field effects that can affect the transport properties of 2DEG, leading to a more generalized theory. Thus in this study, we were able to demonstrate that using Floquet-Drude conductivity method, one can derive a more general

mathematical model which fits better with experiment for the charge transport properties of quantum Hall systems.

VII. CONCLUSIONS

predicting spelling

high-intensity

In this paper, we introduced a generalized mathematical model for predicting charge transport properties in a 2DEG under a nonoscillating magnetic field and a high intensity light. Under the uniform magnetic field, the charged particles can only settle in discrete energy values which leads to the Landau quantization. We modeled the behavior of electrons in Landau levels under the dressing field utilizing the Floquet-Drude conductivity method. We assumed the impurities in the material as a Gaussian random scattering potential. Finally, we de-

rived expressions for x-directional and y-directional longitudinal components of electric conductivity for the considered system.

calculations spelling

Our derived analytical expressions transport characteristics of the dressed quantum Hall system can be controlled by the applied dressing field's intensity. Using detailed numerical calculations with empirical system parameters, we further analyzed the manipulation of conductivity components using the dressing field. We found that the graphical illustrations that we obtained from these numerical calculations are capable of producing the same behavior as experiments on quantum Hall systems in the absence of a dressing field. Furthermore, we identified that by increasing the intensity of the radiation, the conductivity regions near the Landau levels can be the behavior being identified in previous works, their results did not coincide with the more accurate description of conductivity components in undressed quantum Hall systems. However, our generalized analysis on conductivity components of quantum Hall systems provide a well-suited description for these specific quantum Hall systems.

adapted

In summary, the primary purpose of this study was to broaden the modern descriptions on transport properties of dressed quantum Hall systems. Moreover, our detailed theoretical analysis showed that the recently introduced Floquet-Drude conductivity model can be adopted to extend the models that were used to describe the transport characteristics of quantum Hall systems. Owing the ability to control the conductivity regions, high intensity external illumination may be used as a trigger for two-dimensional quantum switching devices which are employed as the building blocks of next generation nanoelectronic devices. As a concluding remark, we believe that our findings of this paper can be used towards understanding the 2D optoelectronic nano transistors, enhancing their performance, and inventing novel appliances.

optoelectronic

ACKNOWLEDGMENTS

next-generation

K.H. wish to acknowledge the members of AXL at Monash University for their support and specially T.N. Perera for insightful discussions. The authors are grateful to Monash University for their support.

Change the integral notation as per my previous comments. I will not mark them separately.

Appendix A: Wave function solutions for a dressed quantum Hall system

time-dependent

The derivation of the solutions for the time dependent Schrödinger equation with our system's Hamiltonian (Eq. 1) is quite similar to that followed in Refs. [30, 50]. We start with expanding the Hamiltonian for

two-dimensional case

$$\hat{H}_e(t) = \frac{1}{2m_e} \left[[\hat{p}_x + eBy]^2 + \left[\hat{p}_y - \frac{eE}{\omega} \cos(\omega t) \right]^2 \right]. \quad (\text{A1})$$

Since $[\hat{H}_e(t), \hat{p}_x] = 0$, both of these operators share same eigenfunctions $L_x^{-1/2} \exp(\frac{ip_x x}{\hbar})$ where $p_x = 2\pi\hbar m/L_x$ with $m \in \mathbb{Z}$. Thus, we re-arrange the Hamiltonian using the definition of canonical momentum in y -direction and this leads to

$$\hat{H}_e(t) = \frac{1}{2m_e} \left[[p_x + eBy]^2 + \left[-i\hbar \frac{\partial}{\partial y} + \frac{eE}{\omega} \cos(\omega t) \right]^2 \right].$$

Subsequently we define the *center of mass* on the y -axis $y_0 = -p_x/eB$ and the $\omega_0 = eB/m_e$. This leads to a new a Hamiltonian

$$\hat{H}_e(t) = \frac{m_e \omega_0^2}{2} \tilde{y}^2 + \frac{1}{2m_e} \left[-\hbar^2 \frac{\partial^2}{\partial \tilde{y}^2} + \frac{1}{\omega} \frac{d}{dt} \right] \vartheta(\tilde{y}, t), \quad (\text{A3})$$

where we used a variable substitution $\tilde{y} = (y - y_0)$. Furthermore, we assume that the wave function solutions for the time-dependent Schrödinger equation of considered quantum system

$$i\hbar \frac{d\psi}{dt} = \hat{H}_e(t)\psi, \quad (\text{A4})$$

can be presented by the following form

$$\psi_m(x, \tilde{y}, t) = \frac{1}{\sqrt{L_x}} \exp\left(\frac{ip_x x}{\hbar} + \frac{ieE\tilde{y}}{\hbar\omega} \cos(\omega t)\right) \vartheta(\tilde{y}, t), \quad (\text{A5})$$

where $\vartheta(\tilde{y}, t)$ is a function that satisfy the property

$$\left[\frac{m_e \omega_0^2}{2} \tilde{y}^2 - eE\tilde{y} \sin(\omega t) - \frac{\hbar^2}{2m_e} \frac{\partial^2}{\partial \tilde{y}^2} - i\hbar \frac{d}{dt} \right] \vartheta(\tilde{y}, t) = 0. \quad (\text{A6})$$

If we turn off the dressing field ($E = 0$), this equation leads to the Schrödinger equation with the simple harmonic oscillator Hamiltonian

$$i\hbar \frac{d\vartheta(\tilde{y}, t)}{dt} = \left[\frac{\hat{p}_y^2}{2m_e} + \frac{1}{2} m_e \omega_0^2 \tilde{y}^2 \right] \vartheta(\tilde{y}, t). \quad (\text{A7})$$

Thus, we can identify $S(t) \equiv eE \sin(\omega t)$ term as an external force act on the harmonic oscillator, and we can solve this as a forced harmonic oscillator in \tilde{y} axis

$$i\hbar \frac{d\vartheta(\tilde{y}, t)}{dt} = \left[-\frac{\hbar^2}{2m_e} \frac{\partial^2}{\partial \tilde{y}^2} + \frac{1}{2} m_e \omega_0^2 \tilde{y}^2 - \tilde{y} S(t) \right] \vartheta(\tilde{y}, t). \quad (\text{A8})$$

This system is exactly solvable, and we can solve the equation using the methods explained by Husimi [50].

We introduce a time dependent shifted coordinate $y' = \tilde{y} - \zeta(t)$ and perform the following unitary transformation

$$\vartheta(y', t) = \exp\left(\frac{im_e \dot{\zeta} y'}{\hbar}\right) \varphi(y', t). \quad (\text{A9})$$

This leads to

$$i\hbar \frac{\partial \varphi(y', t)}{\partial t} = \left[-\frac{\hbar^2}{2m_e} \frac{\partial^2}{\partial y'^2} + \frac{1}{2} m_e \omega_0^2 y'^2 + [m_e \ddot{\zeta} + m_e \omega_0^2 \zeta - S(t)] y' + \left[-\frac{1}{2} m_e \dot{\zeta}^2 + \frac{1}{2} m_e \omega_0^2 \zeta^2 - \zeta S(t) \right] \right] \varphi(y', t). \quad (\text{A10})$$

Subsequently, we can restrict $\zeta(t)$ function such that

$$m_e \ddot{\zeta} + m_e \omega_0^2 \zeta = S(t), \quad (\text{A11})$$

that simply our previous expression as

$$i\hbar \frac{\partial \varphi(y', t)}{\partial t} = \left[-\frac{\hbar^2}{2m_e} \frac{\partial^2}{\partial y'^2} + \frac{1}{2} m_e \omega_0^2 y'^2 - L(\zeta, \dot{\zeta}, t) \right] \varphi(y', t). \quad (\text{A12})$$

Here

$$L(\zeta, \dot{\zeta}, t) = \frac{1}{2} m_e \dot{\zeta}^2 - \frac{1}{2} m_e \omega_0^2 \zeta^2 + \zeta S(t), \quad (\text{A13})$$

is the Lagrangian of a classical driven oscillator. To proceed further, another unitary transform can be introduced as follows

$$\varphi(y', t) = \exp\left(\frac{i}{\hbar} \int_0^t dt' L(\zeta, \dot{\zeta}, t')\right) \chi(y', t), \quad (\text{A14})$$

and substituting Eq. (A14) back in Eq. (A12) yields

$$i\hbar \frac{\partial}{\partial t} \chi(y', t) = \left[-\frac{\hbar^2}{2m_e} \frac{\partial^2}{\partial y'^2} + \frac{1}{2} m_e \omega_0^2 y'^2 \right] \chi(y', t). \quad (\text{A15})$$

This is the well-known Schrödinger equation of the quantum harmonic oscillator. This allows us to identify the well known eigenfunctions [61, 62]

$$\chi_n(y) = \frac{\sqrt{\kappa}}{\sqrt{2^n n!}} e^{-\kappa^2 y^2 / 2} \mathcal{H}_n(\kappa y), \quad (\text{A16})$$

with eigenvalues

$$\epsilon_n = \hbar \omega_0 \left(n + \frac{1}{2} \right) \text{ for } n \in \mathbb{Z}_0^+. \quad (\text{A17})$$

Here, $\kappa = \sqrt{m_e \omega_0 / \hbar}$, and \mathcal{H}_n are the Hermite polynomials. Thus, we can identify the solutions for Eq. (A8) as

$$\vartheta_n(\tilde{y}, t) = \chi_n(\tilde{y} - \zeta(t)) \exp\left(\frac{i}{\hbar} \left[-\epsilon_n t + m_e \dot{\zeta}(t) [\tilde{y} - \zeta(t)] + \int_0^t dt' L(\zeta, \dot{\zeta}, t') \right]\right). \quad (\text{A18})$$

this issue of you using dots for time derivatives and eq. A4 type full description here is problematic!! Three different possible meanings - total diff, partial diff or something else!

Since $\chi_n(x)$ functions forms a complete set, any general solution $\vartheta(\tilde{y}, t)$ can be presented with the help of the solutions derived in Eq. (A18).

Finally, we consider our scenario where we assumed that $S(t) = eE \sin(\omega t)$, and we derive the solution for Eq. (A11) as

$$\zeta(t) = \frac{eE}{m_e(\omega_0^2 - \omega^2)} \sin(\omega t). \quad (\text{A19})$$

Substituting solutions in Eq. (A18) back in Eq. (A5), we obtain a set of wave functions with two different quantum number (n, m) that satisfy the time dependent Schrödinger equation Eq. (A4) as follows

$$\begin{aligned} \psi_{n,m}(x, y, t) &= \frac{1}{\sqrt{L_x}} \chi_n(y - y_0 - \zeta(t)) \\ &\times \exp\left(\frac{i}{\hbar} \left[-\epsilon_n t + p_x x + \frac{eE[y - y_0]}{\omega} \cos(\omega t) \right. \right. \\ &\quad \left. \left. + m_e \dot{\zeta}(t) [y - y_0 - \zeta(t)] + \int_0^t dt' L(\zeta, \dot{\zeta}, t') \right] \right). \end{aligned} \quad (\text{A20})$$

Appendix B: Floquet modes and quasienergies

1. Position space representation

First we define the time integral of the Lagrangian of the classical oscillator given in Eq. (5), over a period $T = 2\pi/\omega$ as

$$\Delta_\varepsilon = \frac{1}{T} \int_0^T dt' L(\zeta, \dot{\zeta}, t'). \quad (\text{B1})$$

Additionally, performing this integral, we can obtain a more simplified result

$$\Delta_\varepsilon = \frac{(eE)^2}{4m_e(\omega_0^2 - \omega^2)}. \quad (\text{B2})$$

Next, we define another parameter

$$\xi = \int_0^t dt' L(\zeta, \dot{\zeta}, t') - \Delta_\varepsilon t, \quad (\text{B3})$$

and after simplifying, we can identify

$$\xi = \frac{(eE)^2 (3\omega^2 - \omega_0^2)}{8m_e \omega (\omega_0^2 - \omega^2)^2} \sin(2\omega t), \quad (\text{B4})$$

which is a periodic function in time. Using these parameters, we can factorize the wave function given in Eq. (2) as linearly time dependent part and periodic time depen-

dent part as follows

$$\begin{aligned} \psi_\alpha(x, y, t) &= \exp\left(\frac{i}{\hbar} [-\epsilon_n t + \Delta_\varepsilon t]\right) \frac{1}{\sqrt{L_x}} \chi_n(y - y_0 - \zeta(t)) \\ &\times \exp\left(\frac{i}{\hbar} \left[p_x x + \frac{eE y}{\omega} \cos(\omega t) \right. \right. \\ &\quad \left. \left. + m_e \dot{\zeta}(t) [y - \zeta(t)] + \int_0^t dt' L(\zeta, \dot{\zeta}, t') - \Delta_\varepsilon t \right] \right). \end{aligned} \quad (\text{B5})$$

This leads to separate the linear time dependent phase component as the quasienergies

$$\varepsilon_n = \hbar \omega_0 \left(n + \frac{1}{2} \right) - \Delta_\varepsilon, \quad (\text{B6})$$

while rest of the components as time-periodic Floquet modes

$$\begin{aligned} \phi_{n,m}(x, y, t) &= \frac{1}{\sqrt{L_x}} \chi_n(y - y_0 - \zeta(t)) \exp\left(\frac{i}{\hbar} \left[p_x x \right. \right. \\ &\quad \left. \left. + \frac{eE[y - y_0]}{\omega} \cos(\omega t) \right. \right. \\ &\quad \left. \left. + m_e \dot{\zeta}(t) [y - y_0 - \zeta(t)] + \xi \right] \right). \end{aligned} \quad (\text{B7})$$

2. Momentum space representation

We perform continuous Fourier transform over the considering confined space $A = L_x L_y$ on the Floquet modes given in Eq. (7) to realize the Floquet modes in momentum space

$$\begin{aligned} \phi_{n,m}(k_x, k_y, t) &= \exp\left(\frac{-i\gamma(t)}{\hbar} y_0\right) \exp\left(\frac{-i}{\hbar} [m_e \dot{\zeta}(t) \zeta(t) - \xi]\right) \\ &\times \int_{-L_y/2}^{L_y/2} dy \exp(-i[k_y - \gamma(t)]y) \chi_n[y - \mu(t)] \\ &\times \frac{1}{\sqrt{L_x}} \int_{-L_x/2}^{L_x/2} dx \exp(-ik_x x) \exp\left(\frac{ip_x}{\hbar} x\right). \end{aligned} \quad (\text{B8})$$

Here we used new two parameters

$$\mu(t) = \frac{eE \sin(\omega t)}{m_e(\omega_0^2 - \omega^2)} + y_0, \quad (\text{B9})$$

and

$$\gamma(t) = \frac{eE \omega_0^2 \cos(\omega t)}{\hbar \omega (\omega_0^2 - \omega^2)}. \quad (\text{B10})$$

Subsequently, using the Fourier transform identity [49]

$$\int_{L_x} dx \exp\left(-ik_x x + \frac{ip_x}{\hbar} x\right) = L_x \delta_{k_x, \frac{p_x}{\hbar}}, \quad (\text{B11})$$

we can derive

$$\begin{aligned} \phi_{n,m}(k_x, k_y, t) &= \Phi_{n,m}(k_y, t) \delta_{k_x, \frac{p_x}{\hbar}} \\ &\times \exp\left(\frac{-i\gamma(t)}{\hbar} y_0\right) \exp\left(\frac{-i}{\hbar} \left[m_e \dot{\zeta}(t) \zeta(t) - \xi\right]\right), \end{aligned} \quad (\text{B12})$$

where we can define $\Phi_{n,m}(k_y, t)$ as

$$\begin{aligned} \Phi_{n,m}(k_y, t) &= \sqrt{L_x} \int_{-L_y/2}^{L_y/2} dy \chi_n[y - \mu(t)] \\ &\times \exp(-i[k_y - \gamma(t)]y). \end{aligned} \quad (\text{B13})$$

Substituting $k'_y = k_y - \gamma(t)$ with $y' = y - \mu(t)$, and assuming that the size of the considered 2DEG sample in y -direction is considerably large ($L_y \rightarrow \infty$), we can obtain

$$\Phi_{n,m}(k'_y, t) = \sqrt{L_x} e^{-ik'_y \mu} \int_{-\infty}^{\infty} dy' \chi_n(y') \exp(-ik'_y y'). \quad (\text{B14})$$

Moreover, we can identify that the above integral represents the Fourier transform of $\{\chi_n\}$ functions. In addition, using the symmetric conditions of the Fourier transform for Gauss-Hermite functions $\theta_n(x)$ [63]

$$\mathcal{FT}[\theta_n(\kappa x), x, k] = \frac{i^n}{|\kappa|} \theta_n(k/\kappa), \quad (\text{B15})$$

we can simply the Eq. (B14) as

$$\Phi_{n,m}(k'_y, t) = \sqrt{L_x} e^{-ik'_y \mu} \tilde{\chi}_n(k'_y), \quad (\text{B16})$$

with

$$\tilde{\chi}_n(k) = \frac{i^n}{\sqrt{2^n n! \sqrt{\pi}}} \left(\frac{1}{\kappa}\right)^{1/2} e^{-\frac{k^2}{2\kappa^2}} \mathcal{H}_n\left(\frac{k}{\kappa}\right). \quad (\text{B17})$$

Finally, substitute Eq. (B16) back into Eq. (B12) and this leads to

$$\begin{aligned} \phi_{n,m}(k_x, k_y, t) &= \sqrt{L_x} \tilde{\chi}_n(k_y - b \cos(\omega t)) \\ &\times \exp\left(i\xi - ik_y \left[d \sin(\omega t) + \frac{\hbar k_x}{eB}\right]\right), \end{aligned} \quad (\text{B18})$$

where

$$b \equiv \frac{eE\omega_0^2}{\hbar\omega(\omega_0^2 - \omega^2)}, \quad (\text{B19})$$

and

$$d \equiv \frac{eE}{m_e(\omega_0^2 - \omega^2)}. \quad (\text{B20})$$

It is necessary to notice that k_x is quantized with $k_x = 2\pi m/L_x$, $m \in \mathbb{Z}$.

Appendix C: Floquet-Fermi golden rule for a dressed quantum Hall system

The Floquet-Fermi golden rule for our dressed quantum Hall system is derived using the t - t' formalism. The t - t' -Floquet states [31, 33]

$$|\psi_{n,m}(t, t')\rangle = \exp\left(-\frac{i}{\hbar} \varepsilon_n t\right) |\phi_{n,m}(t')\rangle, \quad (\text{C1})$$

are derived by separating the aperiodic and periodic components of the Floquet states given in Eq. (14). Additionally, these states fulfill the t - t' -Schrödinger equation [31, 33]

$$i\hbar \frac{\partial}{\partial t} |\psi_{n,m}(t, t')\rangle = H_F(t') |\psi_{n,m}(t, t')\rangle, \quad (\text{C2})$$

where *Floquet Hamiltonian* defined as

$$H_F(t') = H_e(t') - i\hbar \frac{\partial}{\partial t'}. \quad (\text{C3})$$

Next, we can identify the time evolution operator corresponding to the t - t' -Schrödinger equation as

$$U_F(t, t_0; t') = \exp\left(-\frac{i}{\hbar} H_F(t')[t - t_0]\right). \quad (\text{C4})$$

The advantage of t - t' formalism lies on this time evolution operator which avoids any time ordering operators [31].

For our scenario, we take into account a time-independent total perturbation $V(\mathbf{r})$ which has been turned on at the reference time $t = t_0$, and the t - t' -Schrödinger equation becomes

$$i\hbar \frac{\partial}{\partial t} |\Psi_{n,m}(t, t')\rangle = [H_F(t') + V(\mathbf{r})] |\Psi_{n,m}(t, t')\rangle. \quad (\text{C5})$$

This introduces a new wave function solution $|\Psi_{n,m}\rangle$ for a system with a given perturbation. If $t \leq t_0$, both of the solutions for Eq. (C2) and Eq. (C5) coincide

$$|\psi_{n,m}(t, t')\rangle = |\Psi_{n,m}(t, t')\rangle \quad \text{when } t \leq t_0. \quad (\text{C6})$$

Next, our analysis can move into the interaction picture representation [48, 49] and in the interaction picture, the t - t' -Floquet state can be identified as

$$|\Psi_{n,m}(t, t')\rangle_I = U_0^\dagger(t, t_0; t') |\Psi_{n,m}(t, t')\rangle. \quad (\text{C7})$$

Due to time independence, the perturbation in the interaction picture has the same form as Schrödinger picture representation

$$V_I(\mathbf{r}) = U_0^\dagger(t, t_0; t') V(\mathbf{r}) U_0(t, t_0; t') = V(\mathbf{r}). \quad (\text{C8})$$

This leads us to the t - t' -Schrödinger equation in the interaction picture representation

$$i\hbar \frac{\partial}{\partial t} |\Psi_{n,m}(t, t')\rangle_I = V_I(\mathbf{r}) |\Psi_{n,m}(t, t')\rangle_I, \quad (\text{C9})$$

with the recursive solutions [48, 49]

$$\begin{aligned} |\Psi_{n,m}(t, t')\rangle_I &= |\Psi_{n,m}(t_0, t')\rangle_I \\ &+ \frac{1}{i\hbar} \int_{t_0}^t dt_1 V_I(\mathbf{r}) |\Psi_{n,m}(t_1, t')\rangle_I. \end{aligned} \quad (\text{C10})$$

Iterating the solution only up to the first order (Born approximation) we obtain

$$\begin{aligned} |\Psi_{n,m}(t, t')\rangle_I &\approx |\psi_{n,m}(t_0, t')\rangle \\ &+ \frac{1}{i\hbar} \int_{t_0}^t dt_1 V_I(\mathbf{r}) |\psi_{n,m}(t_0, t')\rangle. \end{aligned} \quad (\text{C11})$$

Since our t - t' -Floquet states create a basis, we can represent solutions for the t - t' -Schrödinger equation given in Eq. (C5) using our known t - t' -Floquet states

$$|\Psi_\alpha(t, t')\rangle = \sum_\beta a_{\alpha,\beta}(t, t') |\psi_\beta(t, t')\rangle. \quad (\text{C12})$$

Here, we used a single term notation to represent two quantum numbers; $\alpha \equiv (n_\alpha, m_\alpha)$ and $\beta \equiv (n_\beta, m_\beta)$. Then we can identify the *scattering amplitude* as $a_{\alpha,\beta}(t, t') = \langle \psi_\beta(t, t') | \Psi_\alpha(t, t') \rangle$ and this can be evaluated with

$$\begin{aligned} a_{\alpha,\beta}(t, t') &= \langle \psi_\beta(t, t') | \psi_\alpha(t, t') \rangle \\ &+ \frac{1}{i\hbar} \int_{t_0}^t dt_1 \langle \psi_\beta(t_1, t') | V(\mathbf{r}) | \psi_\alpha(t_1, t') \rangle. \end{aligned} \quad (\text{C13})$$

Since the t - t' -Floquet states are orthonormal and assuming $t_0 = 0$ and $\alpha \neq \beta$ this leads to

$$a_{\alpha,\beta}(t, t') = -\frac{i}{\hbar} \int_0^t dt_1 \langle \psi_\beta(t_1, t') | V(\mathbf{r}) | \psi_\alpha(t_1, t') \rangle. \quad (\text{C14})$$

Next, we consider a scattering phenomenon when a electron scatters from a known t - t' -Floquet state $|\psi_\beta(t, t')\rangle$ into a distinct t - t' -Floquet state $|\Psi_\alpha(t, t')\rangle$ with a constant quansienrgy ε as follows

$$\begin{aligned} |\psi_\beta(t, t')\rangle &= \exp\left(-\frac{i}{\hbar}\varepsilon_\beta t\right) |\phi_\beta(t')\rangle \\ &\xrightarrow{\text{scattering}} |\Psi_\alpha(t, t')\rangle = \exp\left(-\frac{i}{\hbar}\varepsilon t\right) |\Phi_\alpha(t')\rangle. \end{aligned} \quad (\text{C15})$$

This scenario is illustared in Fig. 6. The scattering amplitude for this scattering scenario can be calculated using the equation derived in Eq. (C14)

$$a_{\alpha,\beta}(t, t') = -\frac{i}{\hbar} \int_0^t dt_1 e^{\frac{i}{\hbar}(\varepsilon_\beta - \varepsilon)t_1} \langle \phi_\beta(t') | V(\mathbf{r}) | \phi_\alpha(t') \rangle. \quad (\text{C16})$$

By assuming for a long time $t \rightarrow \infty$, we can turn this integral into a delta distribution

$$a_{\alpha,\beta}(t') = -2\pi i \delta(\varepsilon_\beta - \varepsilon) Q, \quad (\text{C17})$$

where $Q = \langle \phi_\beta(t') | V(\mathbf{r}) | \phi_\alpha(t') \rangle$ and using the completeness properties we can re-write this as

$$Q = \sum_{\mathbf{k}} \sum_{\mathbf{k}'} \langle \phi_\beta(t') | \mathbf{k}' \rangle \langle \mathbf{k}' | V(\mathbf{r}) | \mathbf{k} \rangle \langle \mathbf{k} | \phi_\alpha(t') \rangle. \quad (\text{C18})$$

Moreover, separating x -directional and y -directional momentum components, this can be simplified as

$$Q = \sum_{k_x} \sum_{k'_x} \int_{-\infty}^{\infty} \int_{-\infty}^{\infty} dk_y dk'_y V_{\mathbf{k}', \mathbf{k}} \phi_\beta^\dagger(\mathbf{k}', t') \phi_\alpha(\mathbf{k}, t'), \quad (\text{C19})$$

with $V_{\mathbf{k}', \mathbf{k}} \equiv \langle \mathbf{k}' | V(\mathbf{r}) | \mathbf{k} \rangle$.

Since we are presenting the the perturbation potential $V(\mathbf{r})$ by a group of randomly distributed impurities, we take into account N_{imp} number of identical single impurity potentials distributed at randomly but in fixed positions \mathbf{r}_i . Then scattering potential $V(\mathbf{r})$ can be identified as the sum of uncorrelated single impurity potentials $v(\mathbf{r})$

$$V(\mathbf{r}) \equiv \sum_{i=1}^{N_{imp}} v(\mathbf{r} - \mathbf{r}_i). \quad (\text{C20})$$

Furthermore, we model the perturbation $V(\mathbf{r})$ as a Gaussian random potential where one can choose the zero of energy such that the potential is zero on average. This model is characterized by [64]

$$\langle v(\mathbf{r}) \rangle_{imp} = 0, \quad (\text{C21a})$$

$$\langle v(\mathbf{r}) v(\mathbf{r}') \rangle_{imp} = \Upsilon(\mathbf{r} - \mathbf{r}'), \quad (\text{C21b})$$

where $\langle \cdot \rangle_{imp}$ represents the average over the impurity disorder and $\Upsilon(\mathbf{r} - \mathbf{r}')$ is any decaying function depends only on $\mathbf{r} - \mathbf{r}'$. In addition, this model assumes that $v(\mathbf{r} - \mathbf{r}')$ only depends on the magnitude of the position difference $|\mathbf{r} - \mathbf{r}'|$, and it decays with a characteristic length r_c . Since this study considers the case where the wavelength of radiation or scattering electron is much greater than r_c , it is a better approximation to make two-point correlation function to be

$$\langle v(\mathbf{r}) v(\mathbf{r}') \rangle_{imp} = \Upsilon_{imp}^2 \delta(\mathbf{r} - \mathbf{r}'), \quad (\text{C22})$$



FIG. 6. Scattering from known $|\psi_\beta(t, t')\rangle$ state to a constant energy state $|\Psi_\alpha(t, t')\rangle$ due to the scattering potential created by impurities in the material.

where Υ_{imp}^2 is a constant. A random potential $V(\mathbf{r})$ with this property is called white noise [64]. Then we can approximately model the total scattering potential as

$$V(\mathbf{r}) = \sum_{i=1}^{N_{imp}} \Upsilon_{imp} \delta(\mathbf{r} - \mathbf{r}_i). \quad (\text{C23})$$

Here we can identify the Υ_{imp} as the strength of the delta potential. Furthermore, we can calculate $V_{\mathbf{k}', \mathbf{k}}$ using this assumption as follows

$$V_{\mathbf{k}', \mathbf{k}} = \left\langle \mathbf{k}' \left| \sum_{i=1}^{N_{imp}} \Upsilon_{imp} \delta(\mathbf{r} - \mathbf{r}_i) \right| \mathbf{k} \right\rangle \quad (\text{C24a})$$

$$= \sum_{i=1}^{N_{imp}} \int_{-\infty}^{\infty} dy \left[\frac{1}{\sqrt{L_x L_y}} e^{ik'_y y} \delta(y - y_i) \times \frac{1}{\sqrt{L_x L_y}} e^{-ik_y y} \langle k'_x | \Upsilon_{imp} \delta(x - x_i) | k_x \rangle \right] \quad (\text{C24b})$$

$$= \sum_{i=1}^{N_{imp}} \frac{1}{L_x L_y} e^{i(k'_y - k_y)y} \langle k'_x | \Upsilon_{imp} \delta(x - x_i) | k_x \rangle. \quad (\text{C24c})$$

Since $v(\mathbf{r})$ in momentum space is a constant value, each impurity produce same impurity potential for every x -directional momentum pairs. Additionally, assuming the total number of scatters N_{imp} is microscopically large, we can derive

$$V_{\mathbf{k}', \mathbf{k}} = V_{k'_x, k_x} \frac{N_{imp}}{L_y L_x} \int_{-\infty}^{\infty} dy_i e^{i(k'_y - k_y)y_i} \quad (\text{C25a})$$

$$= \eta_{imp} V_{k'_x, k_x} \delta(k'_y - k_y). \quad (\text{C25b})$$

In the above equation we introduced

$$V_{k'_x, k_x} \equiv \langle k'_x | \Upsilon_{imp} \delta(x - x_i) | k_x \rangle, \quad (\text{C26})$$

which is a constant value for every i impurity. Moreover, η_{imp} is the number of impurities in a unit area. It is important to note that $\langle x | k_x \rangle = e^{-ik_x x}$.

Now using Eq. (10) and Eq. (C25b) on Eq. (C19), we obtain

$$Q = \sum_{k_x} \sum_{k'_x} \eta_{imp} V_{k'_x, k_x} \int_{-\infty}^{\infty} \int_{-\infty}^{\infty} dk_y dk'_y \delta(k'_y - k_y) \times \sqrt{L_x} \exp(ik'_y [d \sin(\omega t) + y'_0]) \tilde{\chi}_{n_\beta}(k'_y - b \cos(\omega t)) \times \sqrt{L_x} \exp(-ik_y [d \sin(\omega t) + y_0]) \tilde{\chi}_{n_\alpha}(k_y - b \cos(\omega t)). \quad (\text{C27})$$

Here we have changed the time variable $t' \rightarrow t$ only for the simplicity of notation. This can be simplified as

$$Q = \sum_{k_x} \sum_{k'_x} \eta_{imp} L_x V_{k'_x, k_x} I, \quad (\text{C28})$$

with

$$I = \int_{-\infty}^{\infty} dk_y \tilde{\chi}_{n_\beta}(k_y - b \cos(\omega t)) \tilde{\chi}_{n_\alpha}(k_y - b \cos(\omega t)) \times \exp(-ik_y [y_0 - y'_0]). \quad (\text{C29})$$

To avoid the energy exchange from the dressing field and electrons in Landau levels, the applied radiation must be a purely dressing field. Therefore, in this study we assume that the dressing field can only renormalize the the probability of electron scattering inside a same Landau energy level ($n_\alpha = n_\beta = N$). This transform the Eq. (C29) to

$$I = \int_{-\infty}^{\infty} dk_y \tilde{\chi}_N^2(k_y - b \cos(\omega t)) \exp(-ik_y [y_0 - y'_0]). \quad (\text{C30})$$

Using the Fourier transform of Gauss-Hermite functions [63] and the convolution theorem [65, 66] we obtain

$$I = 2\pi \exp(b[y'_0 - y_0] \cos(\omega t)) \times \int_{-\infty}^{\infty} dy \chi_N(y) \chi_N(y_0 - y'_0 - y). \quad (\text{C31})$$

Finally, the scattering amplitude derived in Eq. (C17) can be evaluated for given $k_x = 2\pi m_\alpha / L_x$ and $k'_x = 2\pi m_\beta / L_x$ as

$$a_{\alpha\beta}(k_x, k'_x, t) = -2\pi i \eta_{imp} L_x V_{k'_x, k_x} \delta(\varepsilon_N - \varepsilon) \times \exp(b[y'_0 - y_0] \cos(\omega t)) \times \int_{-\infty}^{\infty} dy \chi_N(y) \chi_N(y_0 - y'_0 - y). \quad (\text{C32})$$

Since this scattering amplitude is time-periodic we can write this as a Fourier series expansion

$$a_{\alpha\beta}(k_x, k'_x, t) = \sum_{l=-\infty}^{\infty} a_{\alpha\beta}^l(k_x, k'_x) e^{-il\omega t}. \quad (\text{C33})$$

In addition, using Jacobi-Anger expansion [67, 68]

$$e^{iz \cos(\theta)} = \sum_{l=-\infty}^{\infty} i^l J_l(z) e^{-il\theta}, \quad (\text{C34})$$

where $J_l(\cdot)$ are Bessel functions of the first kind with l -th integer order, we can re-write the Eq. (C32) as follows

$$a_{\alpha\beta}(k_x, k'_x, t) = \sum_{l=-\infty}^{\infty} -2\pi i^{l+1} \eta_{imp} L_x V_{k'_x, k_x} \delta(\varepsilon_N - \varepsilon) \times J_l(b[y'_0 - y_0]) \times \int_{-\infty}^{\infty} dy \chi_N(y) \chi_N(y_0 - y'_0 - y) e^{-il\omega t}. \quad (\text{C35})$$

Thus, we can identify the Fourier series component of the

scattering amplitude as

$$\begin{aligned} a_{\alpha\beta}^l(k_x, k'_x) = & -2\pi i^{l+1} \eta_{imp} L_x V_{k'_x, k_x} \\ & \times \delta(\varepsilon_N - \varepsilon) J_l(b[y'_0 - y_0]) \\ & \times \int_{-\infty}^{\infty} dy \chi_{n_\beta}(y) \chi_{n_\beta}(y_0 - y'_0 - y). \end{aligned} \quad (C36)$$

Furthermore, we define *transition probability matrix* as

$$(A_{\alpha\beta})^{l,l'} \equiv a_{\alpha\beta}^l [a_{\alpha\beta}^{l'}]^*, \quad (C37)$$

and this becomes

$$\begin{aligned} (A_{\alpha\beta})^{l,l'}(k_x, k'_x) = & [2\pi \eta_{imp} L_x |V_{k'_x, k_x}|^2 \delta^2(\varepsilon_N - \varepsilon) \\ & \times J_l(b[y'_0 - y_0]) J_{l'}(g[y'_0 - y_0]) \\ & \times \left| \int_{-\infty}^{\infty} dy \chi_{n_\beta}(y) \chi_{n_\beta}(y_0 - y'_0 - y) \right|^2]. \end{aligned} \quad (C38)$$

Then describing the square of the delta distribution using the following interpretation [26, 30]

$$\delta^2(\varepsilon) = \delta(\varepsilon) \delta(0) = \frac{\delta(\varepsilon)}{2\pi\hbar} \int_{-t/2}^{t/2} e^{i0 \times t'/\hbar} dt' = \frac{\delta(\varepsilon)t}{2\pi\hbar}, \quad (C39)$$

and executing the time derivation operation on each matrix element of transition probability matrix, we receive the *transition amplitude matrix* elements

$$\begin{aligned} \Gamma_{\alpha\beta}^{ll'}(k_x, k'_x) = & \frac{2\pi \eta_{imp}^2 L_x^2}{\hbar} |V_{k'_x, k_x}|^2 \delta(\varepsilon_\beta - \varepsilon) \\ & \times J_l(b[y'_0 - y_0]) J_{l'}(g[y'_0 - y_0]) \\ & \times \left| \int_{-\infty}^{\infty} dy \chi_N(y) \chi_N(y_0 - y'_0 - y) \right|^2. \end{aligned} \quad (C40)$$

Additionally, the inverse scattering time matrix can be identified as the sum of all available momentum over the impurity averaged transition probability matrix element [31, 59]

$$\left(\frac{1}{\tau(\varepsilon, k_x)} \right)_{\alpha\beta}^{ll'} = \frac{1}{L_x} \sum_{k'_x} \langle \Gamma_{\alpha\beta}^{ll'}(k'_x, k_x) \rangle_{imp}. \quad (C41)$$

Next, applying the 1-dimensional momentum continuum limit $\sum_{k'_x} \rightarrow L_x/2\pi \int dk'_x$, we can obtain

$$\begin{aligned} \left(\frac{1}{\tau(\varepsilon, k_x)} \right)_{\alpha\beta}^{ll'} = & \frac{2\pi \eta_{imp}^2 L_x^2}{\hbar} \frac{V_{imp}}{2\pi} \delta(\varepsilon_\beta - \varepsilon) \\ = & \int_{-\infty}^{\infty} dk'_x J_l \left(\frac{b\hbar}{eB} [k_x - k'_x] \right) J_{l'} \left(\frac{b\hbar}{eB} [k_x - k'_x] \right) \\ & \times \left| \int_{-\infty}^{\infty} dy \chi_{n_\beta}(y) \chi_{n_\beta} \left(\frac{\hbar}{eB} [k'_x - k_x] - y \right) \right|^2. \end{aligned} \quad (C42)$$

Here an impurity average of white noise potential allows to identify $\langle |V_{k'_x, k_x}|^2 \rangle_{imp} = V_{imp}$. Finally, using substitutions $k'_x = k_1$ and $y = \hbar k_2/eB$, we can derive our expression for the inverse scattering time matrix for N -th Landau level as follows

$$\begin{aligned} & \left(\frac{1}{\tau(\varepsilon, k_x)} \right)_N^{ll'} \\ = & \frac{\eta_{imp}^2 L_x^2 \hbar V_{imp}}{(eB)^2} \delta(\varepsilon - \varepsilon_N) \\ & \times \int_{-\infty}^{\infty} dk_1 J_l \left(\frac{b\hbar}{eB} [k_x - k_1] \right) J_{l'} \left(\frac{b\hbar}{eB} [k_x - k_1] \right) \\ & \times \left| \int_{-\infty}^{\infty} dk_2 \chi_N \left(\frac{\hbar}{eB} k_2 \right) \chi_N \left(\frac{\hbar}{eB} [k_1 - k_x - k_2] \right) \right|^2. \end{aligned} \quad (C43)$$

Appendix D: Current operators for a dressed quantum Hall system

In this section, we derive the current density operator for the N -th Landau level in a dressed quantum Hall system. We already found the exact solution for our time dependent Hamiltonian give in Eq. (1) and we identified them as the Floquet states in Eq. (14). The Floquet modes derived in Eq. (10) can be represented as quantum states using their corresponding quantum numbers for the simplicity of notation as follows

$$|\phi_{n,m}\rangle = |n, k_x\rangle. \quad (D1)$$

Using this complete set of states [31, 33, 53], we can represent the current operator's matrix element as

$$(j)_{nm, n'm'} \equiv \langle n, k_x | \hat{j} | n', k'_x \rangle. \quad (D2)$$

Thus, the particle current operator for our system [48, 49] can be identified as

$$\hat{j} = \frac{1}{\tilde{m}} (\hat{\mathbf{p}} - e[\mathbf{A}_s + \mathbf{A}_d(t)]), \quad (D3)$$

where \tilde{m} is the mass of the considering particle.

First, we consider the x -directional current operator component, and we can identify that the x -directional current operator as

$$\hat{j}_x = \frac{1}{\tilde{m}} \left(-i\hbar \frac{\partial}{\partial x} + eBy \right). \quad (D4)$$

Next, we calculate the matrix elements of x -directional current operator in Floquet mode basis

$$(j_x)_{nm, n'm'} = \langle n, k_x | \frac{1}{\tilde{m}} \left(-i\hbar \frac{\partial}{\partial x} + eBy \right) | n', k'_x \rangle, \quad (D5)$$

why this tilde is too small?

and we evaluate these using the Floquet modes derived in Eq. (7) as follows

$$(j_x)_{nm,n'm'} = \frac{1}{\tilde{m}} \delta_{k_x, k'_x} \int dy \left[[\hbar k'_x + eBy] \times \chi_n(y - y_0 - \zeta(t)) \chi_{n'}(y - y_0 - \zeta(t)) \right]. \quad (D6)$$

Let $(y - y_0 - \zeta(t)) = \bar{y}$ and we can obtain

$$(j_x)_{nm,n'm'} = \frac{1}{\tilde{m}} \delta_{k_x, k'_x} \int d\bar{y} \left[[\hbar k'_x + eB\bar{y} - \hbar k'_x + eB\zeta(t)] \times \chi_n(\bar{y}) \chi_{n'}(\bar{y}) \right]. \quad (D7)$$

Using the following integral identities of the Floquet modes which are made up with Gauss-Hermite functions [69–70]

For a electric current operator, we can apply the electron's charge and the effective mass of the electron to the above derived equation. This leads to

$$(j_{s=0}^x)_{nm,n'm'}^{electron} = \frac{e^2 B}{m_e} \delta_{k_x, k'_x} \times \left(\sqrt{\frac{n+1}{2}} \delta_{n',n+1} + \sqrt{\frac{n}{2}} \delta_{n',n-1} \right). \quad (D11)$$

Moreover, we can identify the y -directional current operator component as

can you cite the following papers if possible? (not at one point though.)

1. [Theory and technology of SPASERS](#)

M Premaratne, MI Stockman - *Advances in Optics and Photonics*, 2017

2. [Open resonator electric spaser](#)

B Liu, W Zhu, SD Gunapala, MI Stockman... - *ACS nano*, 2017

3. [Direct and third-body mediated resonance energy transfer in dimensionally constrained nanostructures](#)

D Weeraddana, M Premaratne, DL Andrews - *Physical Review B*, 2015

4. [MoS2 spaser](#)

C Jayasekara, M Premaratne, SD Gunapala... - *Journal of Applied Physics*, 2016

$$(j_{s=0}^x)_{nm,n'm'} = \frac{eD}{\tilde{m}} \delta_{k_x, k'_x} \times \left(\sqrt{\frac{n+1}{2}} \delta_{n',n+1} + \sqrt{\frac{n}{2}} \delta_{n',n-1} \right). \quad (D10)$$

$$(j_{s=0}^y)_{nm,n'm'} = \frac{e\tau v}{m_e} \delta_{k_x, k'_x} \times \left[\sqrt{\frac{n}{2}} \delta_{n',n-1} - \sqrt{\frac{n+1}{2}} \delta_{n',n+1} \right]. \quad (D14)$$

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